

## ➤ General Description

This PAP2015S P-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent  $R_{ds(On)}$  performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

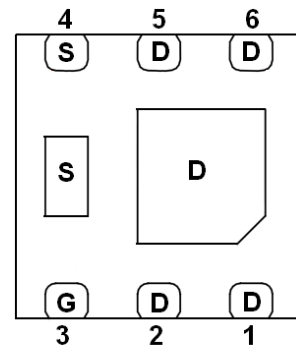
## ➤ Feature

- Super high density cell design for extremely low  $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- DFN2X2-6L package design

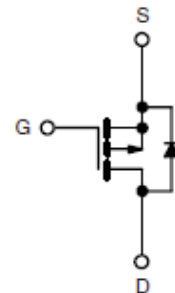
## ➤ Application

- Load Switch, PA Switch and Battery Switch for Portable Devices

## ➤ DFN2X2-6L



BOTTOM VIEW



P-Channel MOSFET

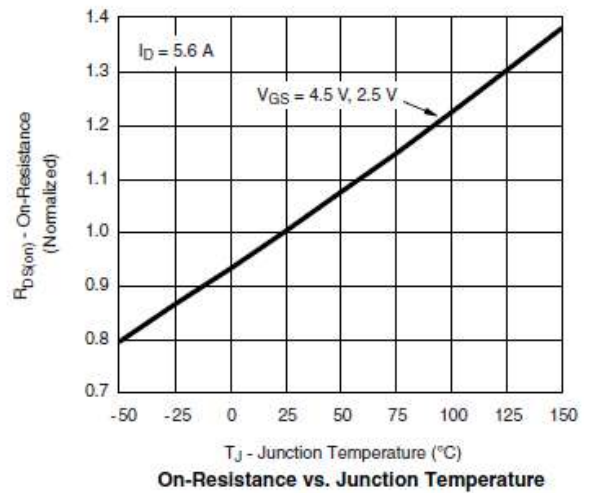
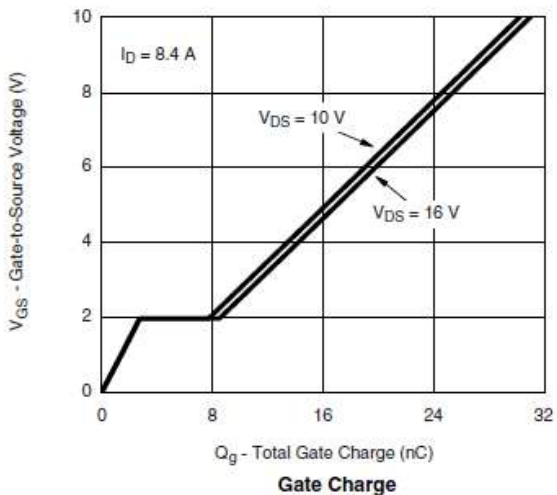
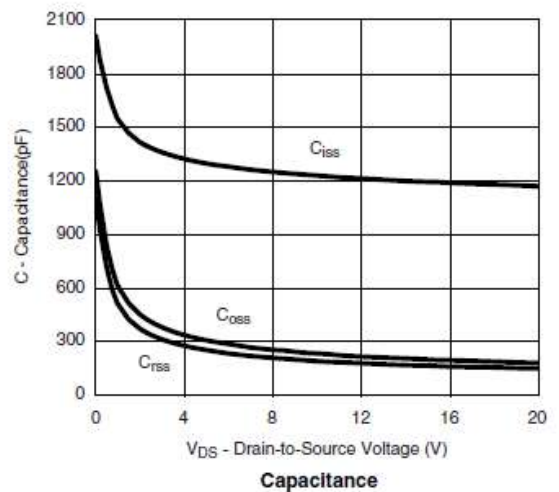
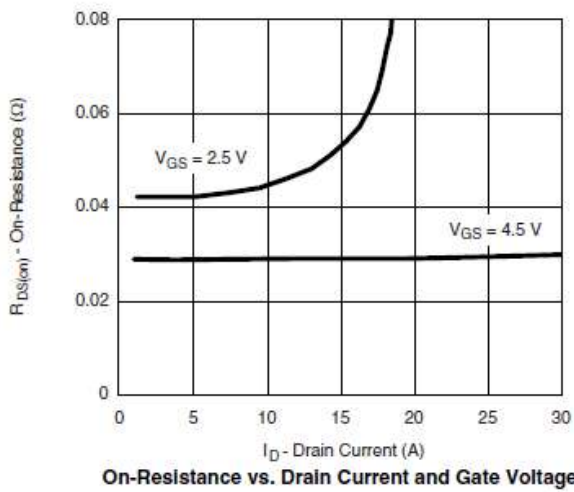
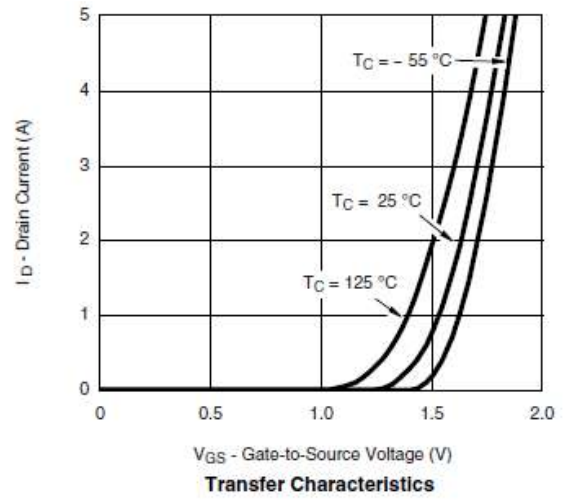
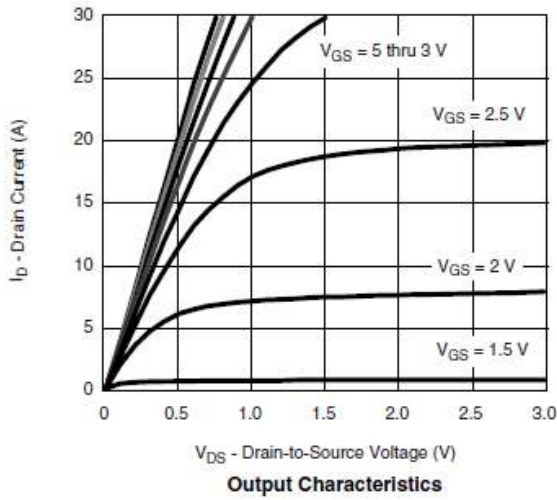
## ➤ Absolute Maximum Ratings

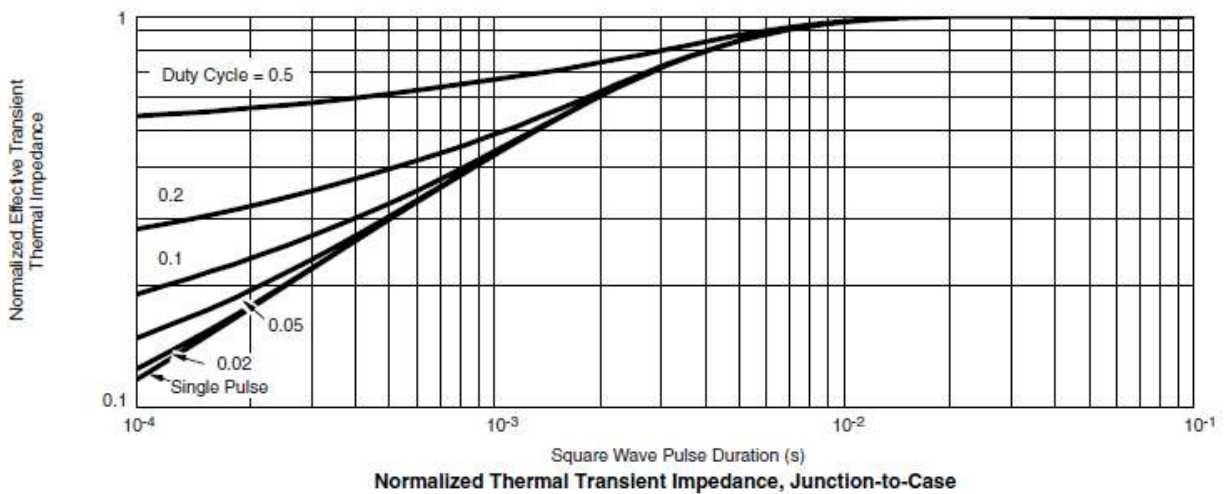
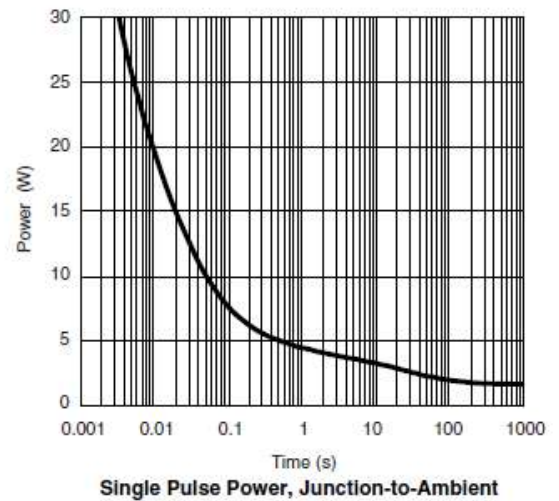
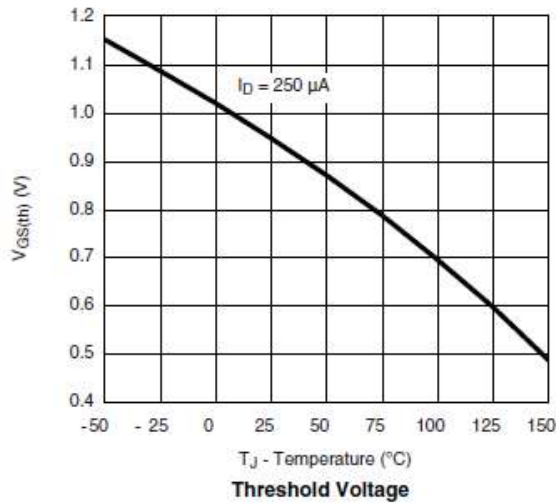
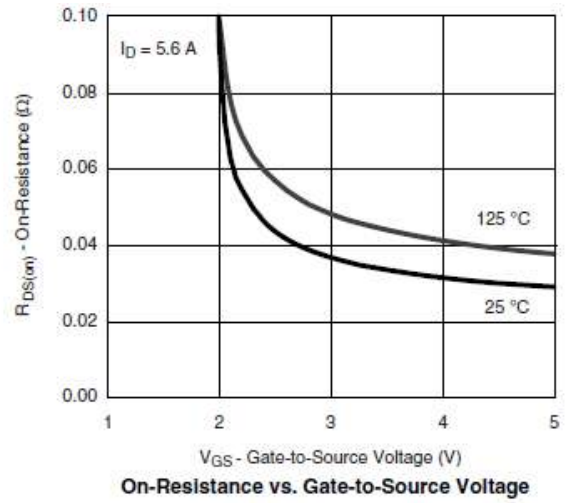
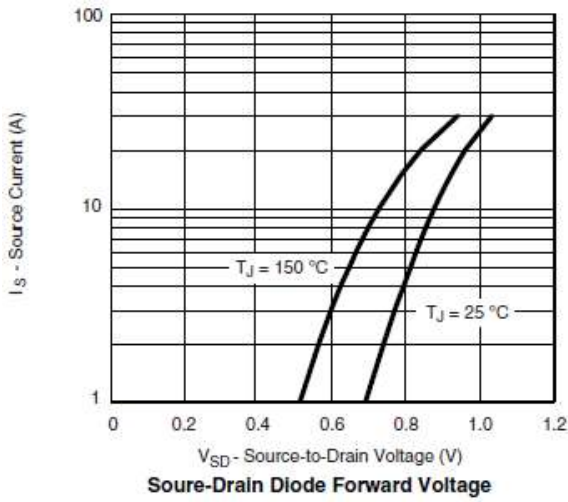
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DSS}$	-20	V
Gate -Source Voltage	$V_{GSS}$	$\pm 12$	V
Continuous Drain Current( $T_J=150^\circ C$ )	$I_D$	$T_A=25^\circ C$	-8.4
		$T_A=70^\circ C$	-6.7
Pulsed Drain Current	$I_{DM}$	-30	A
Continuous Source Current(Diode Conduction)	$I_S$	-2.9	A
Power Dissipation	$P_D$	$T_A=25^\circ C$	2.5
		$T_A=70^\circ C$	2.2
Operating Junction Temperature	$T_J$	150	$^\circ C$
Storage Temperature Range	$T_{STG}$	-55/150	$^\circ C$
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	36	$^\circ C/W$

#### ➤ Electrical Characteristics ( $T_A=25^\circ C$ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.5		-1.0	
Gate Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 12V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-16V, V_{GS}=0V$			-1	uA
		$V_{DS}=-16V, V_{GS}=0V$ $T_J=85^\circ C$			-30	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \leq -5V, V_{GS}=-4.5V$	-20			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-5.6A$		24	32	m $\Omega$
		$V_{GS}=-2.5V, I_D=-2.8A$		33	42	
		$V_{GS}=-1.8V, I_D=-2.0A$		48	60	
Forward Transconductance	$g_{FS}$	$V_{DS}=-10V, I_D=-5.6A$		20		S
Diode Forward Voltage	$V_{SD}$	$I_S=-1.25A, V_{GS}=0V$		-0.75	-1.3	V
<b>Dynamic</b>						
Total Gate Charge	$Q_g$	$V_{DS}=-10V, V_{GS}=-4.5V$ $I_D=-8.4A$		15	25	nC
Gate-Source Charge	$Q_{gs}$			3		
Gate-Drain Charge	$Q_{gd}$			5		
Input Capacitance	$C_{iss}$	$V_{DS}=-10V, V_{GS}=0V$ $f=1MHz$		1250		pF
Output Capacitance	$C_{oss}$			300		
Reverse Transfer Capacitance	$C_{riss}$			200		
Turn-On Time	$t_{d(on)}$	$V_{DD}=-10V, R_L=1.5\Omega$ $I_D=-6.7A, V_{GEN}=-4.5V$ $R_G=1\Omega$		25	50	ns
	$t_r$			50	90	
Turn-Off Time	$t_{d(off)}$			40	75	
	$t_f$			20	40	

## ➤ Typical Characteristics





## ➤ Recommand IR Reflow Soldering Thermal Profile

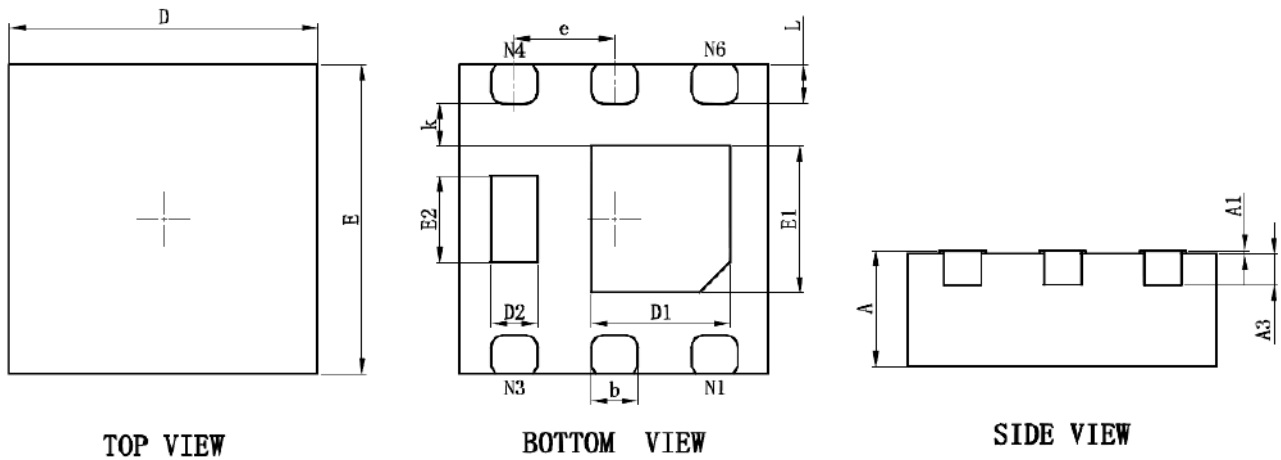


Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T <sub>smin</sub> )	150°C
Temperature Max. (T <sub>smax</sub> )	200°C
Time (t <sub>s</sub> ) from (T <sub>smin</sub> to T <sub>smax</sub> )	60-120 seconds
Average Ramp-up Rate (t <sub>L</sub> to t <sub>P</sub> )	3°C/second max.
Liquidous Temperature (T <sub>L</sub> )	217°C
Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> )	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (t <sub>P</sub> ) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> )	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

## ➤ Ordering Information

Part Number	Description	Quantity
PAP2015S	DFN2X2-6L Reel	4000 pcs

➤ **Package Information (DFN2X2-6L)**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	1.924	2.076	0.076	0.082
E	1.924	2.076	0.076	0.082
D1	0.800	1.000	0.031	0.039
E1	0.850	1.050	0.033	0.041
D2	0.200	0.400	0.008	0.016
E2	0.460	0.660	0.018	0.026
k	0.200MIN.		0.008MIN.	
b	0.250	0.350	0.010	0.014
e	0.650TYP.		0.026TYP.	
L	0.174	0.326	0.007	0.013

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